

# BUL39D

# HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

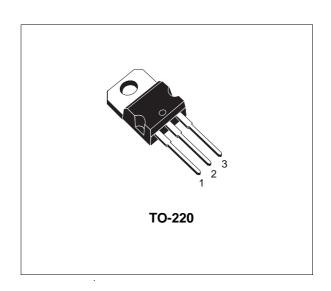
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- HIGH RUGGEDNESS

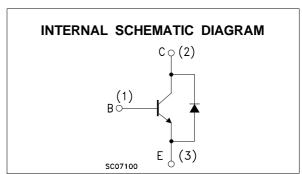
### **APPLICATIONS**

- ELECTRONIC TRANSFORMERS FOR HALOGEN LAMPS
- SWITCH MODE POWER SUPPLIES

#### **DESCRIPTION**

The BUL39D is manufactured using high voltage Multi Epitaxial Planar technology to enhance switching speeds while maintaining wide RBSOA. The BUL series is designed for use in electronics transformers for halogen lamps.





### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit	
V <sub>CES</sub>	Collector-Emitter Voltage (V <sub>BE</sub> = 0)	850	V	
$V_{CEO}$	Collector-Emitter Voltage (IB = 0)	450	V	
$V_{EBO}$	Emitter-Base Voltage (IC = 0)	9	V	
Ic	Collector Current	4	А	
I <sub>CM</sub>	Collector Peak Current (t <sub>p</sub> <5 ms)	8	А	
lΒ	Base Current	2	А	
I <sub>BM</sub>	Base Peak Current (t <sub>p</sub> <5 ms)	4	Α	
P <sub>tot</sub>	Total Dissipation at Tc = 25 °C	70	W	
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C	
Tj	Max. Operating Junction Temperature	150	°C	

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### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-Case	Max	1.78	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-Ambient	Max	70	°C/W

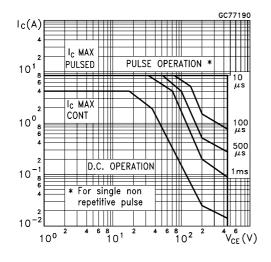
## **ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = rated V <sub>C</sub> V <sub>CE</sub> = rated V <sub>C</sub>				100 500	μΑ μΑ
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 9 V				100	μΑ
V <sub>CEO(sus)</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA	L = 25 mH	450			V
$V_{CE(sat)^*}$	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1 A I <sub>C</sub> = 2.5 A	$I_B = 0.2 A$ $I_B = 0.5 A$		0.13	0.5 1.1	V V
V <sub>BE(sat)</sub> *	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1 A I <sub>C</sub> = 2.5 A	I <sub>B</sub> = 0.2 A I <sub>B</sub> = 0.5 A			1.1 1.3	V V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 5 A I <sub>C</sub> = 10 mA	V <sub>CE</sub> = 10 V V <sub>CE</sub> = 5 V	4 10			
V <sub>CEW</sub>	Maximum Collector Emitter Voltage Without Snubber	IC = 6 A $V_{BB} = -2.5 V$ $t_p = 10 \mu s$	$R_{BB} = 0 \Omega$ L = $50\mu H$	450			V
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	I <sub>C</sub> = 2.5 A V <sub>BE(off)</sub> = -5 V V <sub>CL</sub> = 300 V	$I_{Bon} = 0.5 \text{ A}$ $R_{BB} = 0 \Omega$ $L = 1 \text{ mH}$		0.7 50	1.5 100	μs ns
V <sub>f</sub>	Diode Forward Voltage	I <sub>C</sub> = 2 A				1.5	V

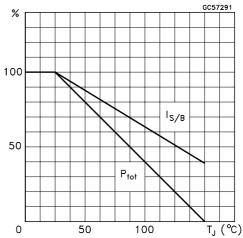
<sup>\*</sup> Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

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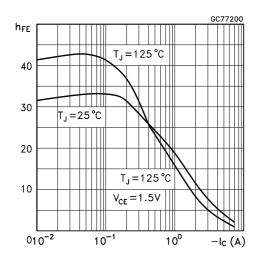
### Safe Operating Areas



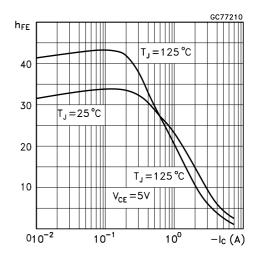
# Derating Curve



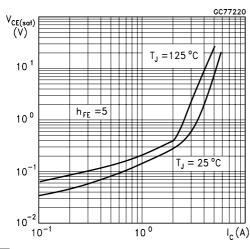
### DC Current Gain



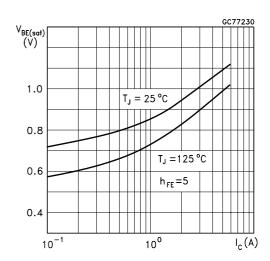
DC Current Gain



### Collector Emitter Saturation Voltage

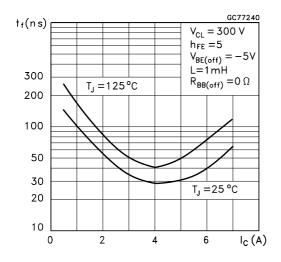


Base Emitter Saturation Voltage

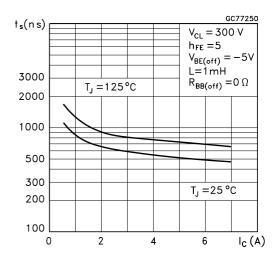


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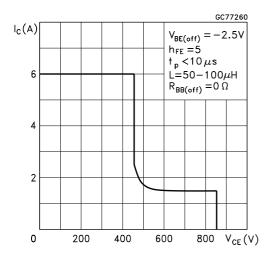
### Inductive Fall Time



### Inductive Storage Time



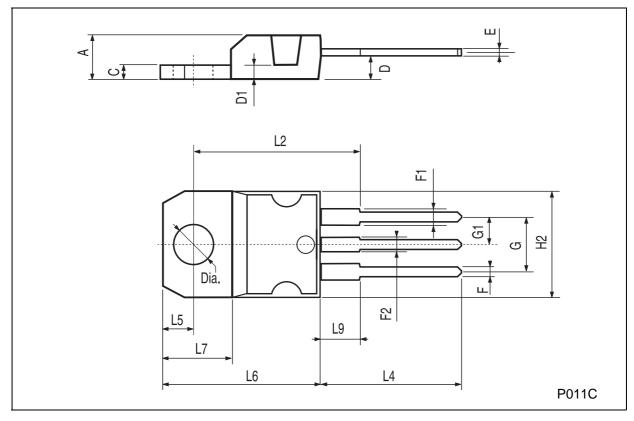
### Reverse Biased SOA



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### **TO-220 MECHANICAL DATA**

DIM.	mm			inch			
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	4.40		4.60	0.173		0.181	
С	1.23		1.32	0.048		0.051	
D	2.40		2.72	0.094		0.107	
D1		1.27			0.050		
E	0.49		0.70	0.019		0.027	
F	0.61		0.88	0.024		0.034	
F1	1.14		1.70	0.044		0.067	
F2	1.14		1.70	0.044		0.067	
G	4.95		5.15	0.194		0.203	
G1	2.4		2.7	0.094		0.106	
H2	10.0		10.40	0.393		0.409	
L2		16.4			0.645		
L4	13.0		14.0	0.511		0.551	
L5	2.65		2.95	0.104		0.116	
L6	15.25		15.75	0.600		0.620	
L7	6.2		6.6	0.244		0.260	
L9	3.5		3.93	0.137		0.154	
DIA.	3.75		3.85	0.147		0.151	



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